L	Hits	Search Text	DB	Time stamp
Number 21	1	6335292.pn.	USPAT	2004/02/05
22	313	Li-Li.in.	USPAT; US-PGPUB;	14:23 2004/02/05 14:23
23	41	Howard-Bradley-J.in.	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/02/05 14:24
24	105	Li-Li.in. and @ay<=1999	DERWENT; IBM_TDB USPAT; US-PGPUB;	2004/02/05 14:24
25	189	same (oxide or SiO or SiO?sub.2))) and	EPO; JPO; DERWENT; IBM_TDB USPAT; EPO; JPO; DERWENT;	2004/02/05 14:25
26	613	(Second adj power) (CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:27
28	523	((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05
29	357	(((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:28
30	328	((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05
31	284	or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor) and ((etch or etching)	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2004/02/05 14:29
32	222	same (SiO or siO?sub.2 or oxide)) (((((CF?sub.4 with CHF?sub.3 with (inert or argon or argon or helium or he)) and plasma) and @ay<=2001) and power) and semiconductor) and ((etch or etching) same (SiO or siO?sub.2 or oxide) same	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/05 14:29
-	1	plasma) 6159794.pn.	USPAT	2003/01/08 09:16
-	17451	plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))	USPAT	2003/04/16
_	160	(plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)	USPAT	2004/02/05 14:24
-	124	((plasma and semiconductor and (etching same (oxide or SiO or SiO?sub.2))) and (second adj power)) and (chlorine or Cl?sub.2 or HBr or bromic or CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or inert or argon or Ar or helium or he)	USPAT	2003/04/16 13:13

_	102	(((plasma and semiconductor and (etching	USPAT	2003/01/08
	102	same (oxide or SiO or SiO?sub.2))) and		13:09
		(second adj power)) and (chlorine or		
		Cl?sub.2 or HBr or bromic or CF?sub.4 or CHF?sub.3 or "CH.sub.2 F.sub.2" or inert		
	:	or argon or Ar or helium or he)) and		
		(argon or Ar or helium or he)		
-	2786	CF?sub.4 with CHF?sub.3	USPAT	2003/04/16
	0045	(272) 4 (1) 2772) 3		13:11
_	2247	(CF?sub.4 with CHF?sub.3) and plasma	USPAT	2003/04/16 13:09
-	452	CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2003/01/08
		argon or argon or helium or he)		14:14
-	372	(CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2004/02/05
		argon or argon or helium or he)) and		14:26
_	260	plasma ((CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2003/01/08
	200	argon or argon or helium or he)) and	OSTITE	13:10
		plasma) and power		
	223	(((CF?sub.4 with CHF?sub.3 with (inert or	USPAT	2003/01/08
		argon or argon or helium or he)) and plasma) and power) and ((etch or etching)		14:26
		same (oxide or SiO or SiO?sub.2))		
_	188	((((CF?sub.4 with CHF?sub.3 with (inert	USPAT	2003/01/08
		or argon or argon or helium or he)) and		13:12
		plasma) and power) and ((etch or etching)		
		same (oxide or SiO or SiO?sub.2))) and (watt or W)		
_	183	(((((CF?sub.4 with CHF?sub.3 with (inert	USPAT	2003/01/08
		or argon or argon or helium or he)) and		13:12
		plasma) and power) and ((etch or etching)		
		same (oxide or SiO or SiO?sub.2))) and (watt or W)) not (((plasma and		
		semiconductor and (etching same (oxide or		
		SiO or SiO?sub.2))) and (second adj		
		power)) and (chlorine or Cl?sub.2 or HBr		
		or bromic or CF?sub.4 or CHF?sub.3 or		
		"CH.sub.2 F.sub.2" or inert or argon or Ar or helium or he))		
_	201	CF?sub.4 with CHF?sub.3 with (helium or	USPAT	2003/01/08
		he)		14:15
-	2	((CF?sub.4 with CHF?sub.3 with (helium or	USPAT	2003/01/08
		he)) and plasma) and ((germanium or Ge) with substrate)		14:15
_	162	(CF?sub.4 with CHF?sub.3 with (helium or	USPAT	2003/01/08
		he)) and plasma		14:22
_	9465	(germanium with substrate) or (gallium	USPAT	2003/01/08
	2021	with arsenide with substrate) ((germanium or Ge) with substrate) and	USPAT	14:23 2003/01/08
	2021	((gallium or Ga) with (arsenide or As or	UDIAI	14:26
		GaAs) with substrate)		
_	883	(((germanium or Ge) with substrate) and	USPAT	2003/01/08
		((gallium or Ga) with (arsenide or As or GaAs) with substrate)) and plasma		14:26
_	1	6159794.pn. and ((etch or etching) same	USPAT	2003/01/08
		(oxide or SiO or SiO?sub.2))		14:27
_	378	((((germanium or Ge) with substrate) and	USPAT	2003/01/08
		((gallium or Ga) with (arsenide or As or		14:27
		GaAs) with substrate)) and plasma) and ((etch or etching) same (oxide or SiO or		
		SiO?sub.2))		
_	210	(((((germanium or Ge) with substrate) and	USPAT	2003/01/08
		((gallium or Ga) with (arsenide or As or		16:19
		GaAs) with substrate)) and plasma) and ((etch or etching) same (oxide or SiO or		
		SiO?sub.2))) and power		
_	40037	(etch or etching) with (oxide or dioxide	USPAT	2003/04/16
_	10220	or SiO or SiO?sub.2)	HCD2m	13:08
-	19320	((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma	USPAT	2003/04/16 13:06
L	l	prasilia		1 = 3 : 0 0

4689	(((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or	USPAT	2003/04/16 13:09
21441	etching)) (etch or etching) with ((silicon adjoxide) or (silicon adj dioxide) or SiO or	USPAT	2003/04/16
3205	SiO?sub.2) ((((etch or etching) with (oxide or	USPAT	2003/04/16
	<pre>and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj</pre>		13.09
2225	<pre>(((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj</pre>	USPAT	2003/04/16 13:10
	dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")		
664	dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3	USPAT	2003/04/16 13:11
541	or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3) ((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma)	USPAT	2003/04/16 13:11
	and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4		
492	((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and	USPAT	2003/04/16 13:17
	(((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and second) and (inert or argon or Ar or	USPAT	2003/04/16 13:14
	21441 3205 2225 664 541	dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) (etch or etching) with ((silicon adjoxide) or (silicon adj dioxide) or SiO?sub.2) 3205 ((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with ((silicon adjoxide) or (silicon adjdioxide) or SiO?sub.2)) (((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adjoxide) or (silicon adjdioxide) or SiO?sub.2)) and ((cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2") (((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2))) and ((cl)sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (cl)sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (Cl)sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF7sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3) ((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((ctch or etching) with ((silicon adjoxide) or (silicon adjoxide) or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adjoxide) or (silicon adjoxide) or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((ctch or etching) with ((silicon adjoxide) or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((ctch or etching) with ((silicon adjoxide) or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((ctch or etching) with ((silicon adjoxide) or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((ctch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((powe	dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) (etch or etching) with ((silicon adjoxide) or (silicon adj dioxide) or SiO?sub.2) 3205 (((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with ((silicon adjoxide) or (silicon adjdioxide) or SiO?sub.2)) ((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) ((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with ((silicon adjoxide) or (silicon adjdioxide) or SiO?sub.2)) and (cl?sub.2 or cl2 or HBr or hydrosibromic or CF4 or CF3sub.4 or CHF3sub.3 or CHF3 or "CH.sub.2 F.sub.2") 664 ((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with ((silicon adjoxide) or (silicon adjdioxide) or SiO or SiO?sub.2)) and (Cl?sub.2 or cl2 or HBr or hydrosibromic or CF4 or CF?sub.4 or CHF?sub.3) 541 ((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and (cl?sub.2 or cl2 or HBr or hydrosibromic or CF4 or CF?sub.4 or CHF?sub.3) 492 ((((((etch or etching) with (oxide or etching))) and ((etch or etching) with (oxide or or cl3 or siO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with (oxide or or cl3 or siO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with (oxide or cl3 or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with (oxide or cl3 or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching)) and ((etch or etching) with (oxide or cl4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 P.sub.2")) and (CF?sub.4 with CHF?sub.3)) and epy<=2001 and second and ((cl?sub.2 or cl2 or HBr or hydrosibromic or cf4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 P.sub.2")) and (cl?sub.2 or cl2 or HBr or h

_	192	<pre>((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or</pre>	USPAT	2003/04/16 13:17
		etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj		
	£	dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3		
	-	or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and (second with power)		*
	179	(((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or	USPAT	2003/04/16
		etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO?sub.2))) and	<u> </u>	
		(Cl?sub.2 or Cl2 or HBr or hydro&1bromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4		
*		with CHF?sub.3)) and @py<=2001) and second) and (inert or argon or Ar or helium or he)) and (second with power)		
_	192	<pre>(((((((((etch or etching) with (oxide or dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or</pre>	USPAT	2003/04/16
		<pre>etching))) and ((etch or etching) with ((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and</pre>		
		(Cl?sub.2 or Cl2 or HBr or hydro&lbromic or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4		
_	60	<pre>with CHF?sub.3)) and @py<=2001) and second) and (second with power) (((((((etch or etching) with (oxide or</pre>	USPAT	2003/04/16
		dioxide or SiO or SiO?sub.2)) and plasma) and ((power or watts) same (etch or etching))) and ((etch or etching) with		13:47
	E	((silicon adj oxide) or (silicon adj dioxide) or SiO or SiO?sub.2))) and (Cl?sub.2 or Cl2 or HBr or hydro&lbromic		
		or CF4 or CF?sub.4 or CHF?sub.3 or CHF3 or "CH.sub.2 F.sub.2")) and (CF?sub.4 with CHF?sub.3)) and @py<=2001) and		
-	2	(second near3 power) 5726449.pn. 5710067.pn.	USPAT	2003/04/16
-	2	5726499.pn. 5710067.pn.	USPAT	13:48 2003/04/16 14:34
-	1	6335292.pn.	USPAT	2003/04/16 15:08
_ [1	6087269.pn.	USPAT	2003/04/16 15:08
	1	6335292.pn.	USPAT	2003/10/10 10:04
_	0	Bradley-Howard.in.	USPAT; US-PGPUB	2003/10/10 10:04
_	0	Bradley-Howard-J.in.	USPAT; US-PGPUB	2003/10/10 10:05
_	208	Li-Li in and places	USPAT; US-PGPUB	2003/10/10 10:05
	124	Li-Li.in. and plamsa Li-Li.in. and (etch or etching)	USPAT; US-PGPUB	2003/10/10 10:06
_	87	Li-Li.in. and plasma	USPAT; US-PGPUB USPAT;	2003/10/10 10:07 2003/10/10
-	25	(Li-Li.in. and (etch or etching)) and	US-PGPUB USPAT;	10:07 2003/10/10
		(Li-Li.in. and plasma) and power	US-PGPUB	10:07

_	179		USPAT	2003/10/10
		same (oxide or SiO or SiO?sub.2))) and		12:55
		(second adj power)		
-	141	((plasma and semiconductor and (etching	USPAT	2003/10/10
		same (oxide or SiO or SiO?sub.2))) and		12:54
		(second adj power)) and @ay<=1999		
-	1	6174451.pn.	USPAT	2003/10/10
		_		11:59
-	109	(plasma and semiconductor and (etching	USPAT	2003/10/10
		same ((silicon adj oxide) or SiO or		12:55
		SiO?sub.2))) and (second adj power)		
_	71	((plasma and semiconductor and (etching	USPAT	2003/10/10
İ		same ((silicon adj oxide) or SiO or		13:43
		SiO?sub.2))) and (second adj power)) and		
		@ay<=1998		
-	2	5726499.pn. 5710067.pn.	USPAT	2003/10/10
				13:44